

# P-Channel 30-V (D-S) MOSFET

PRODU	PRODUCT SUMMARY							
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)					
- 30	$0.0089 \text{ at V}_{GS} = -10 \text{ V}$	- 100	78 nC					
	0.0125 at V <sub>GS</sub> = - 4.5 V	- 90	70110					

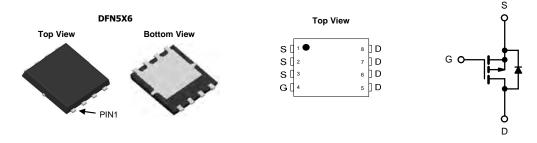
#### **FEATURES**

- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> Tested



#### **APPLICATIONS**

- Notebook
  - Load Switch



P-Channel MOSFET

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	- 30	V	
Gate-Source Voltage		V <sub>GS</sub>		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	I <sub>D</sub>	- 100 <sup>a</sup> - 90 <sup>a</sup> - 31.6 <sup>b, c</sup> - 25.3 <sup>b, c</sup>	
Pulsed Drain Current		I <sub>DM</sub>	- 380	— A
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C T <sub>A</sub> = 25 °C	I <sub>S</sub>	- 80 <sup>a</sup> - 56 <sup>b, c</sup>	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 40	
Single Pulse Avalanche Energy	L = 0.111111	E <sub>AS</sub>	80	mJ
Maximum Power Dissipation	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	P <sub>D</sub>	104 66.6 6.25 <sup>b, c</sup> 4.0 <sup>b, c</sup>	w
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	00	
Soldering Recommendations (Peak Temperature		260	- °C	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 10 s	R <sub>thJA</sub>	15	20	°C/W		
Maximum Junction-to-Case (Drain)	Steady State	$R_{thJC}$	0.9	1.2	C/VV		

#### Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. The DFN5x6 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 54 °C/W.

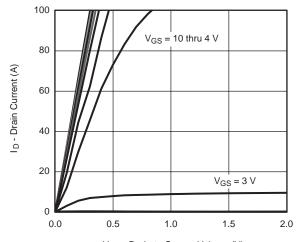


Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	1					
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 30			V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	s/T <sub>J</sub>		- 31		m\//0/
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = - 250 μA		6.5		mV/°(
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	
Zero Gate Voltage Drain Current		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10	μA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 30			Α
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 20 A		0.0089	0.0098	Ω
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 15 A		0.0125	0.0138	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 20 A		95		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			5150		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1215		
Reverse Transfer Capacitance	C <sub>rss</sub>			1125		
Total Gate Charge	Qg	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 20 A		167	250	nC
				78	120	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -20 \text{ A}$		27		
Gate-Drain Charge	$Q_{gd}$			35		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.7		Ω
Turn-On Delay Time	t <sub>d(on)</sub>			25	40	
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$		15	30	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 1.0 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		110	170	
Fall Time	t <sub>f</sub>			30	50	
Turn-On Delay Time	t <sub>d(on)</sub>			110	170	
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$		100	150	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 1.0 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		100	150	
Fall Time	t <sub>f</sub>			50	75	
<b>Drain-Source Body Diode Characteristi</b>	cs					
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			100	۸
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				380	A
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 5 A		- 0.74	- 1.1	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>			50	100	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	L = 3.5.4 dl/dt = 100.4/up. T = 25.90		65	130	nC
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = 3.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		26		
Reverse Recovery Rise Time				24		ns

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$  b. Guaranteed by design, not subject to production testing.

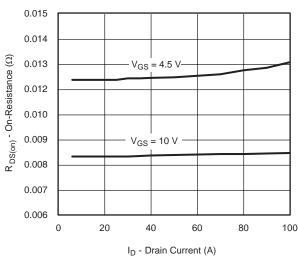
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



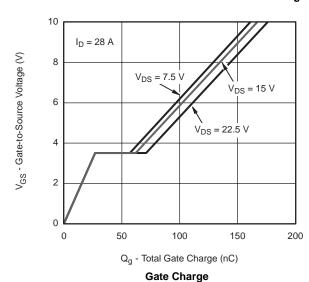


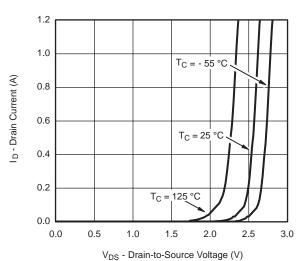
 $V_{\text{DS}}$  - Drain-to-Source Voltage (V)

#### **Output Characteristics**

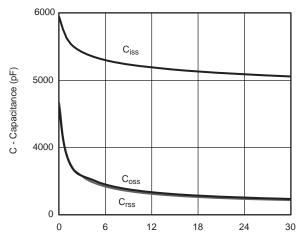


#### On-Resistance vs. Drain Current and Gate Voltage



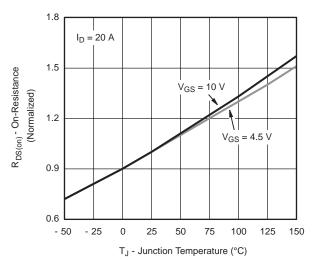


Transfer Characteristics



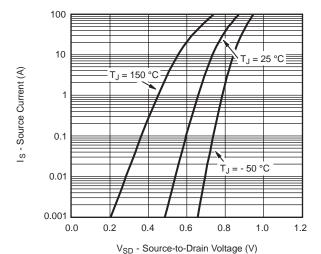
 $V_{\text{DS}}$  - Drain-to-Source Voltage (V)



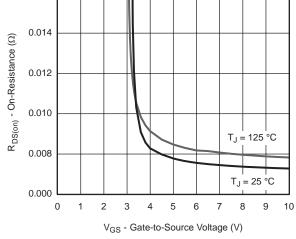


On-Resistance vs. Junction Temperature



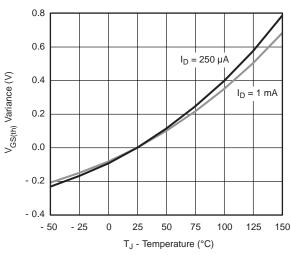


Source-Drain Diode Forward Voltage

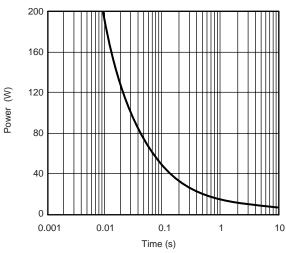


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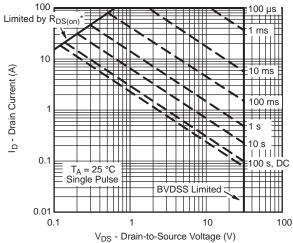
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 



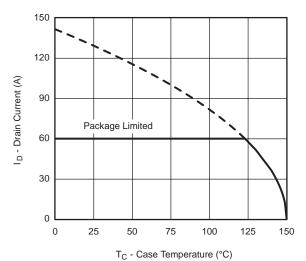
Single Pulse Power, Junction-to-Ambient



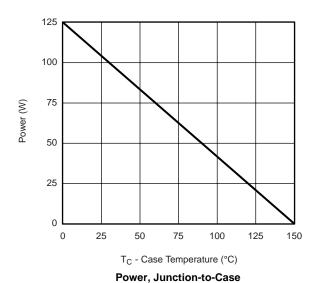
\* V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified

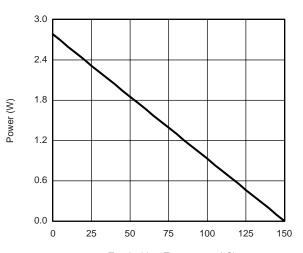
Safe Operating Area, Junction-to-Ambient





### **Current Derating\***



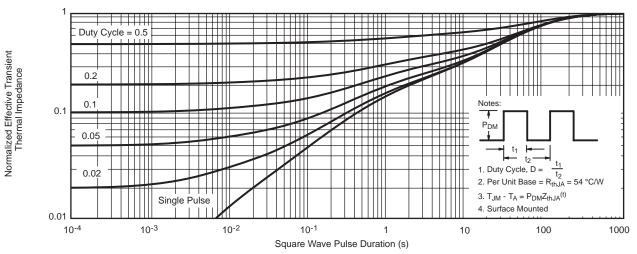


T<sub>A</sub> - Ambient Temperature (°C)

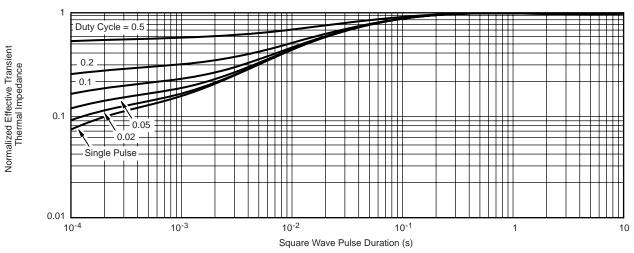
Power, Junction-to-Ambient

 $<sup>^*</sup>$  The power dissipation  $P_D$  is based on  $T_{J(max)}$  = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





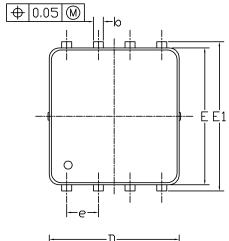
Normalized Thermal Transient Impedance, Junction-to-Ambient

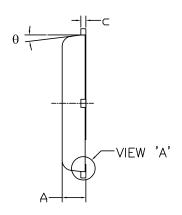


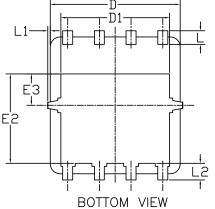
Normalized Thermal Transient Impedance, Junction-to-Case

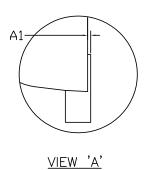






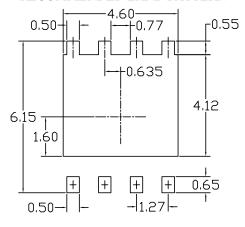






(SCALE 5:1)

RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
3 I MIBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0. 95	1.00	0.033	0.037	0.039	
A1	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0. 15	0. 20	0. 25	0.006	0.008	0.010	
D	4. 80	5. 20	5. 30	0. 201	0. 205	0. 209	
D1	4. 25	4. 35	4. 45	0. 167	0.171	0. 175	
Е	5. 45	5. 55	5. 65	0. 215	0. 219	0. 222	
E1	5. 95	6.05	6. 15	0. 234	0. 238	0. 242	
E2	3. 525	3. 625	3. 725	0. 139	0. 143	0. 147	
E3	1. 175	1. 275	1. 375	0.046	0.050	0.054	
e	1. 27 BSC			0.050 BSC			
L	0.45	0. 55	0.65	0.018	0.022	0.026	
L1	0		0. 15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	

#### **NOTE**

**Din-Tek** 

SEMICONDUCTOR

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
- 2. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

UNIT: mm





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